

FUJI POWER MOSFET Super FAP-G Series

N-CHANNEL SILICON POWER MOSFET

Features

- High speed switching
- Low on-resistance
- No secondary breakdown
- Low driving power
- Avalanche-proof

Applications

- Switching regulators
- UPS (Uninterruptible Power Supply)
- DC-DC converters

Maximum ratings and characteristic Absolute maximum ratings

($T_c=25^\circ\text{C}$ unless otherwise specified)

Item	Symbol	Ratings	Unit	
Drain-source voltage	V_{DS}	200	V	
	V_{DSX}^*5	170	V	
Continuous drain current	I_D	± 45	A	
Pulsed drain current	$I_{D(puls)}$	± 180	A	
Gate-source voltage	V_{GS}	± 30	V	
Non-repetitive Avalanche current	I_{AS}^*2	45	A	
Maximum Avalanche Energy	E_{AS}^*1	258.9	mJ	
Maximum Drain-Source dV/dt	dV_{DS}/dt^*4	20	kV/ μs	
Peak Diode Recovery dV/dt	dV/dt^*3	5	kV/ μs	
Max. power dissipation	P_D	$T_a=25^\circ\text{C}$	2.02	W
		$T_c=25^\circ\text{C}$	270	
Operating and storage temperature range	T_{ch}	+150	$^\circ\text{C}$	
	T_{stg}	-55 to +150	$^\circ\text{C}$	

*1 $L=205\mu\text{H}$, $V_{CC}=48\text{V}$, $T_c=25^\circ\text{C}$, See to avalanche Energy Graph *2 $T_{ch} \leq 150^\circ\text{C}$

*3 $I_F \leq -I_D$, $-di/dt=50\text{A}/\mu\text{s}$, $V_{CC} \leq BV_{DSS}$, $T_{ch} \leq 150^\circ\text{C}$ *4 $V_{DS} \leq 200\text{V}$ *5 $V_{GS}=-30\text{V}$

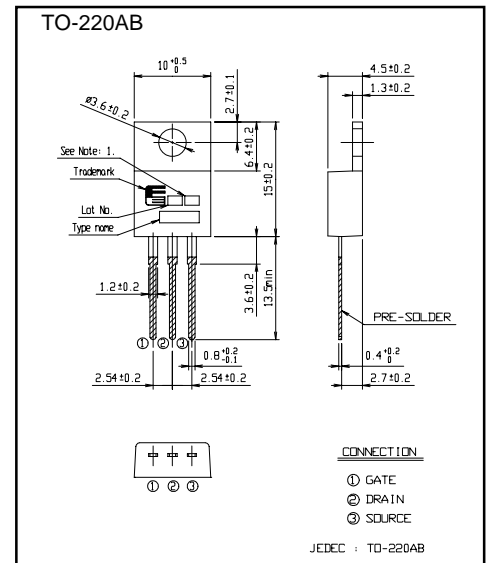
Electrical characteristics ($T_c = 25^\circ\text{C}$ unless otherwise specified)

Item	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Drain-source breakdown voltage	$V_{(BR)DSS}$	$I_D=250\mu\text{A}$ $V_{GS}=0\text{V}$	200			V
Gate threshold voltage	$V_{GS(th)}$	$I_D=250\mu\text{A}$ $V_{DS}=V_{GS}$	3.0		5.0	V
Zero gate voltage drain current	I_{DSS}	$V_{DS}=200\text{V}$ $V_{GS}=0\text{V}$			25	μA
		$V_{DS}=160\text{V}$ $V_{GS}=0\text{V}$			250	
Gate-source leakage current	I_{GSS}	$V_{GS}=\pm 30\text{V}$ $V_{DS}=0\text{V}$		10	100	nA
Drain-source on-state resistance	$R_{DS(on)}$	$I_D=15\text{A}$ $V_{GS}=10\text{V}$		50	66	$\text{m}\Omega$
Forward transconductance	g_{fs}	$I_D=15\text{A}$ $V_{DS}=25\text{V}$	12.5	25		S
Input capacitance	C_{iss}	$V_{DS}=75\text{V}$		1960	2940	pF
Output capacitance	C_{oss}	$V_{GS}=0\text{V}$		260	390	
Reverse transfer capacitance	C_{rss}	$f=1\text{MHz}$		18	27	
Turn-on time t_{on}	$t_{d(on)}$	$V_{CC}=48\text{V}$ $I_D=15\text{A}$		20	30	ns
	t_r	$V_{GS}=10\text{V}$		17	26	
Turn-off time t_{off}	$t_{d(off)}$	$R_{GS}=10\Omega$		53	80	
	t_f			19	29	
Total Gate Charge	Q_G	$V_{CC}=100\text{V}$		51	76.5	nC
Gate-Source Charge	Q_{GS}	$I_D=30\text{A}$		15	22.5	
Gate-Drain Charge	Q_{GD}	$V_{GS}=10\text{V}$		16	24	
Avalanche capability	I_{AV}	$L=205\mu\text{H}$ $T_{ch}=25^\circ\text{C}$	45			A
Diode forward on-voltage	V_{SD}	$I_F=30\text{A}$ $V_{GS}=0\text{V}$ $T_{ch}=25^\circ\text{C}$		1.10	1.65	V
Reverse recovery time	t_{rr}	$I_F=30\text{A}$ $V_{GS}=0\text{V}$		0.19		μs
Reverse recovery charge	Q_{rr}	$-di/dt=100\text{A}/\mu\text{s}$ $T_{ch}=25^\circ\text{C}$		1.4		μC

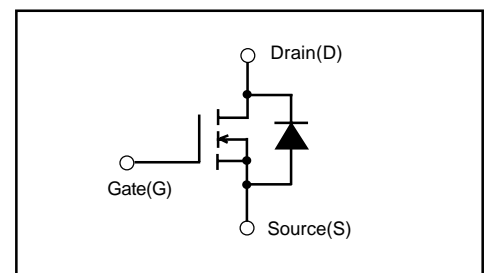
Thermal characteristics

Item	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Thermal resistance	$R_{th(ch-c)}$	channel to case			0.463	$^\circ\text{C}/\text{W}$
	$R_{th(ch-a)}$	channel to ambient			62.0	$^\circ\text{C}/\text{W}$

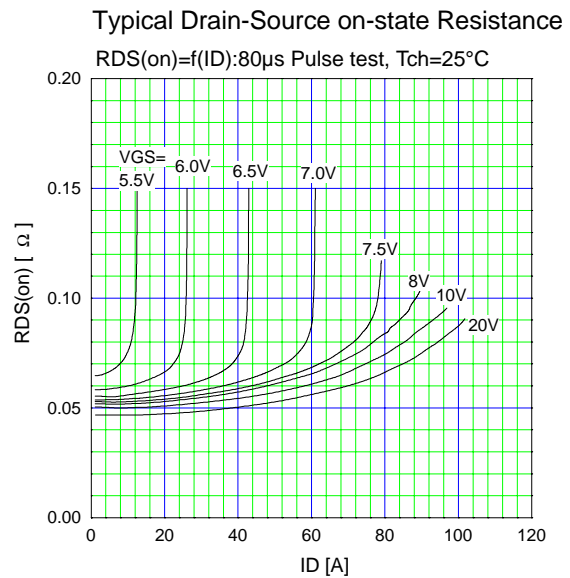
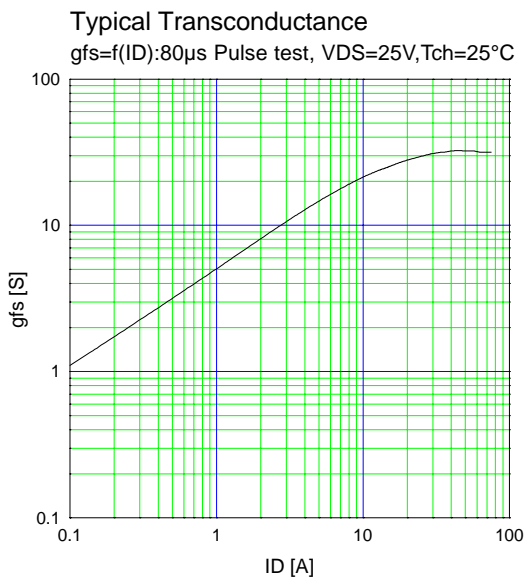
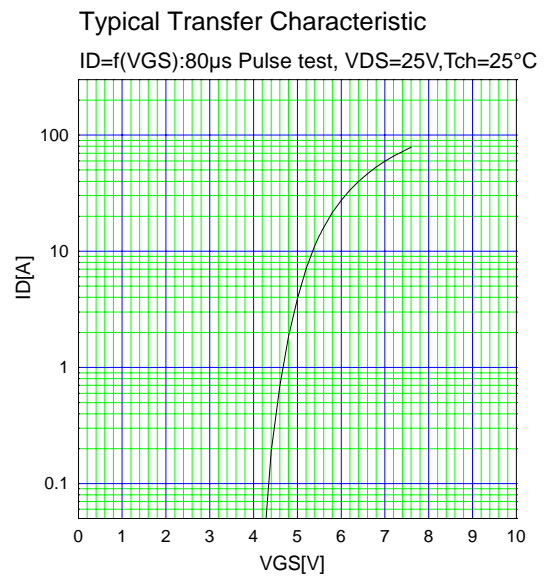
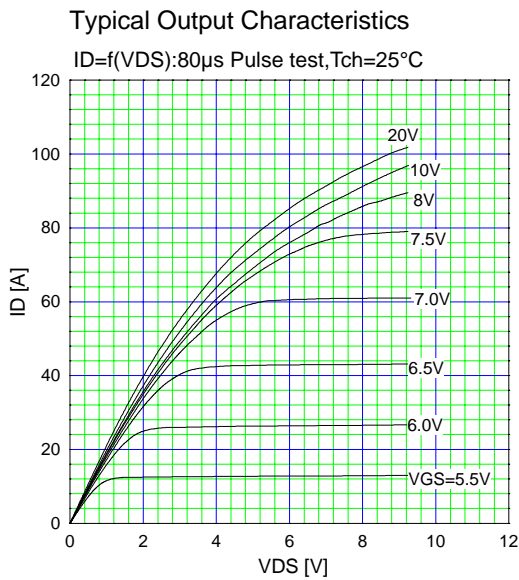
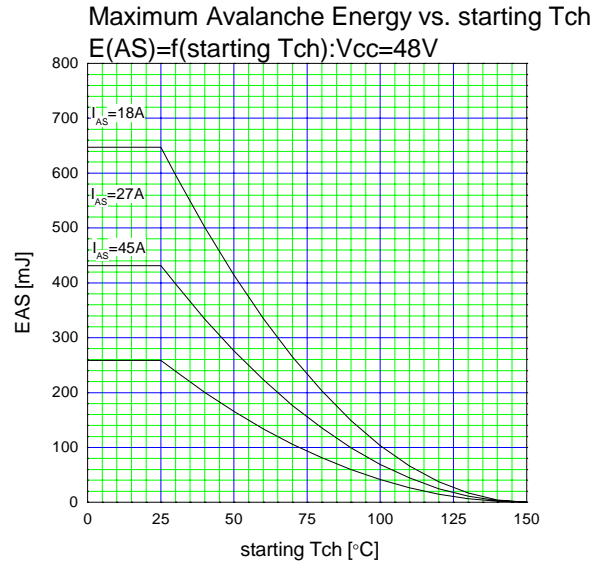
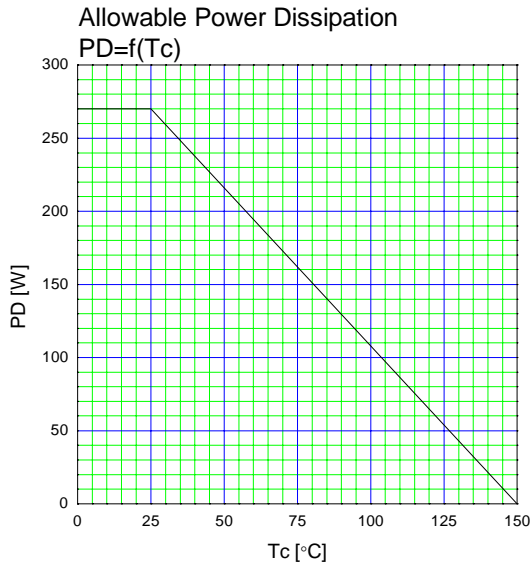
Outline Drawings (mm)



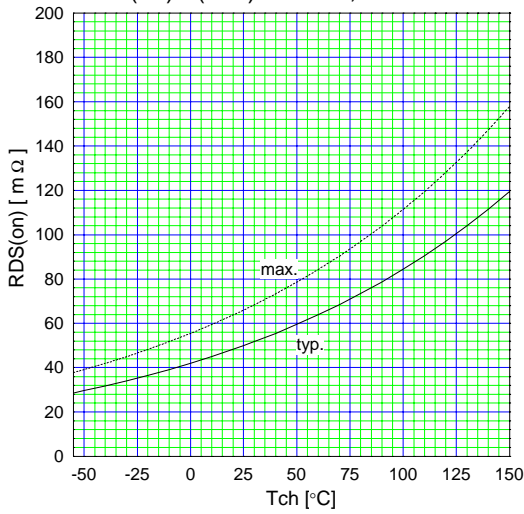
Equivalent circuit schematic



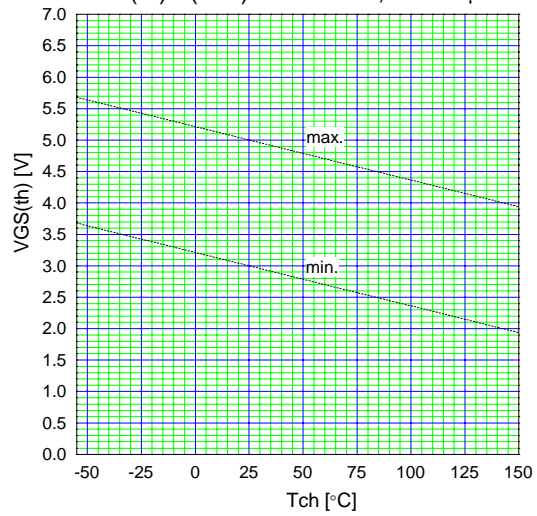
Characteristics



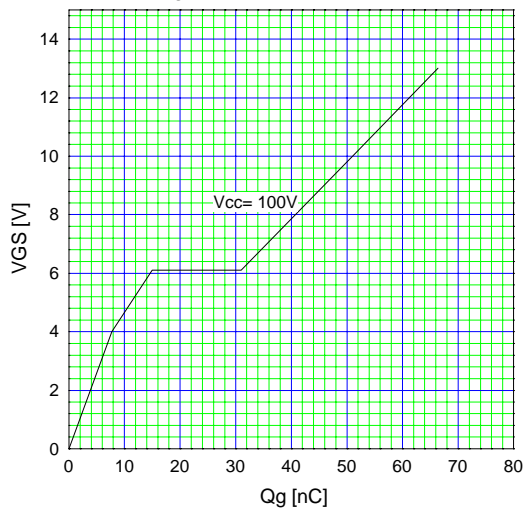
Drain-Source On-state Resistance
 $R_{DS(on)}=f(T_{ch}):I_D=15A, V_{GS}=10V$



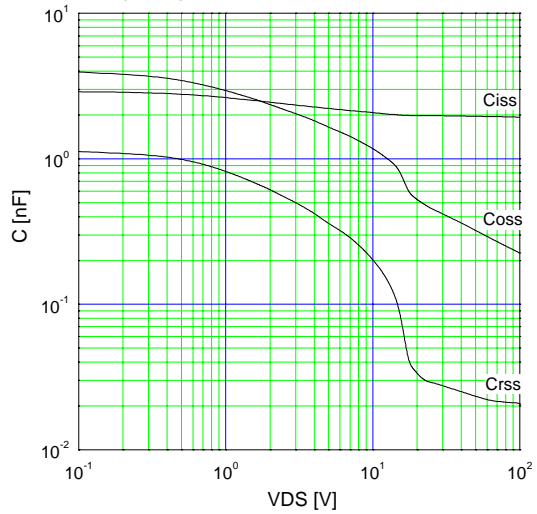
Gate Threshold Voltage vs. Tch
 $V_{GS(th)}=f(T_{ch}):V_{DS}=V_{GS}, I_D=250\mu A$



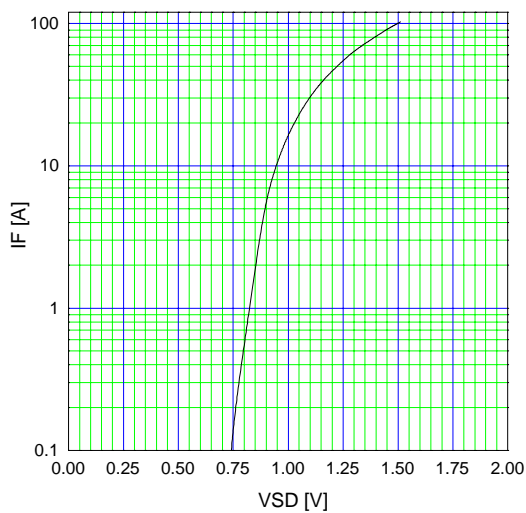
Typical Gate Charge Characteristics
 $V_{GS}=f(Q_g):I_D=30A, T_{ch}=25^\circ C$



Typical Capacitance
 $C=f(V_{DS}):V_{GS}=0V, f=1MHz$



Typical Forward Characteristics of Reverse Diode
 $I_F=f(V_{SD}):80\mu s$ Pulse test, $T_{ch}=25^\circ C$



Typical Switching Characteristics vs. I_D
 $t=f(I_D):V_{CC}=48V, V_{GS}=10V, R_G=10\Omega$

